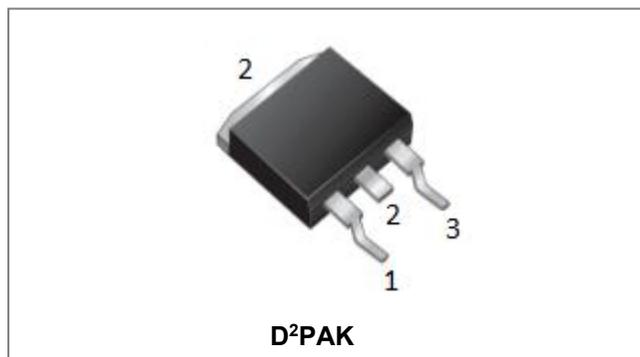


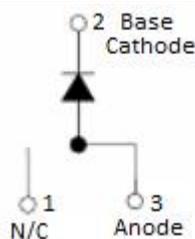
## STB30H100 SCHOTTKY RECTIFIER



### Features

- 175°C T<sub>J</sub> operation
- Ultralow forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Trench MOS Schottky technology
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

### Circuit Diagram



### Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

### Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage	V <sub>RRM</sub>	-	100	V
Working Peak Reverse Voltage	V <sub>RWM</sub>			
DC Blocking Voltage	V <sub>R</sub>			
Average Rectified Forward Current	I <sub>F(AV)</sub>	50% duty cycle @T <sub>c</sub> =100°C, rectangular wave form	30	A
Peak One Cycle Non-Repetitive Surge Current	I <sub>FSM</sub>	8.3ms, Half Sine pulse	300	A

### Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop*	V <sub>F1</sub>	@ 15A, Pulse, T <sub>J</sub> = 25 °C	0.72	0.75	V
		@ 30A, Pulse, T <sub>J</sub> = 25 °C	0.87	0.90	
Reverse Current at DC condition*	I <sub>R1</sub>	@V <sub>R</sub> = rated V <sub>R</sub> T <sub>J</sub> = 25°C	0.006	1	mA
		@V <sub>R</sub> = rated V <sub>R</sub> T <sub>J</sub> = 125°C	2	15	mA
Junction Capacitance	C <sub>T</sub>	@V <sub>R</sub> = 5V, T <sub>C</sub> = 25 °C f <sub>SIG</sub> = 1MHz	800	-	pF

\* Pulse width < 300 μs, duty cycle < 2%

**Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	$T_J$	-	-55 to +175	$^{\circ}\text{C}$
Storage Temperature	$T_{\text{stg}}$	-	-55 to +175	$^{\circ}\text{C}$
Typical Thermal Resistance Junction to Case	$R_{\theta\text{JC}}$	DC operation	2	$^{\circ}\text{C/W}$
Approximate Weight	wt	-	1.85	g

**Ratings and Characteristics Curves**

Figure 1  
Typical Forward Characteristics

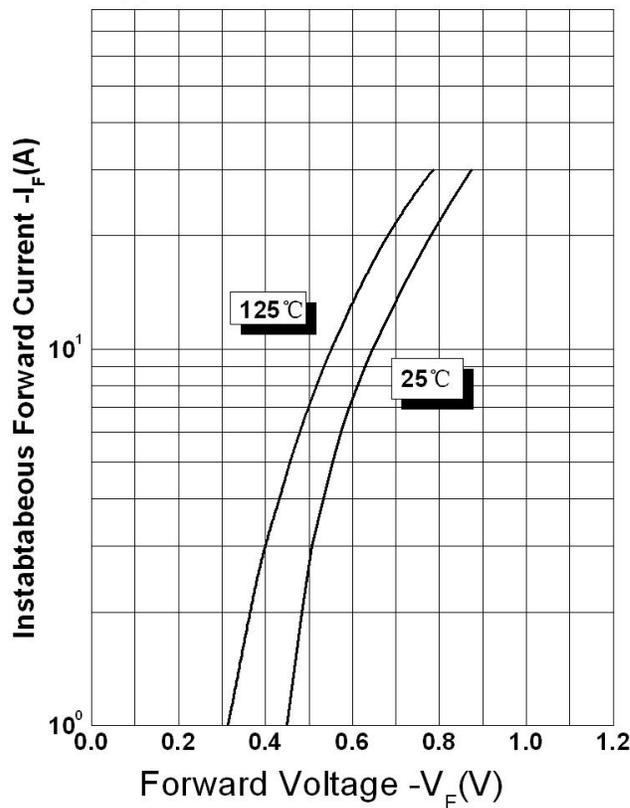


Figure 2  
Typical Reverse Characteristics

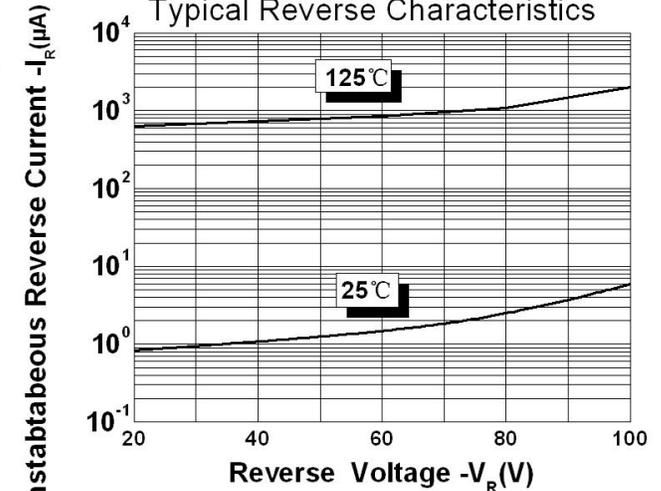
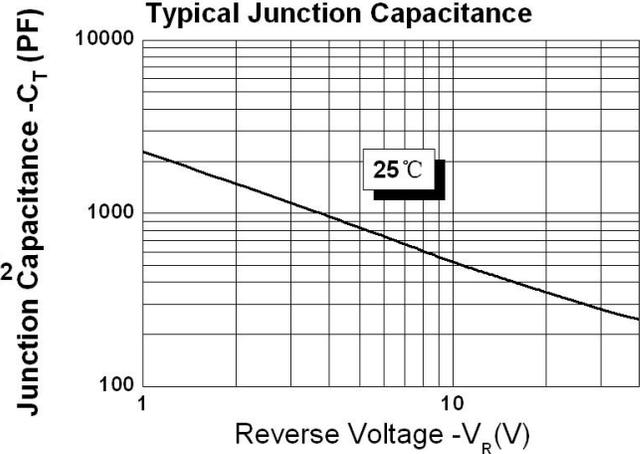
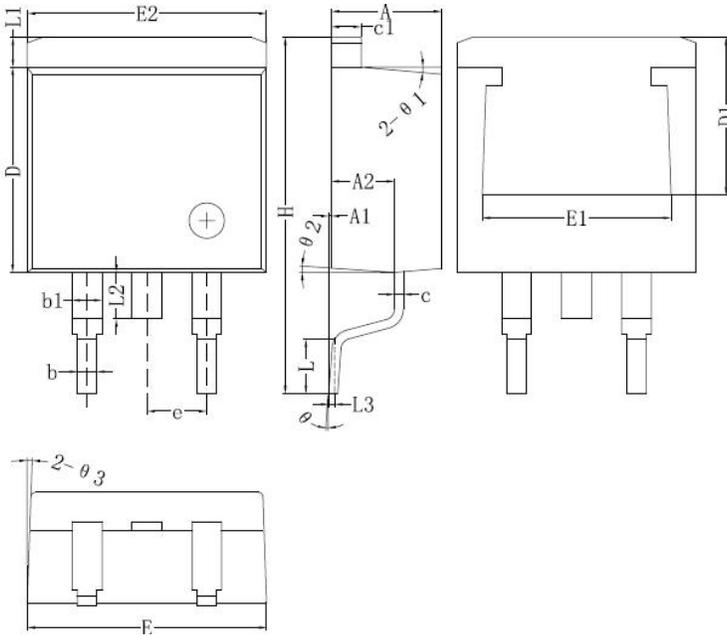


Figure 3  
Typical Junction Capacitance



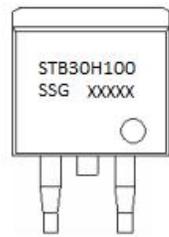
**Mechanical Dimensions D<sup>2</sup>PAK**


Symbol	Dimensions in millimeters		
	Min.	Typical	Max.
A	4.47	4.70	4.85
A1	0	0.10	0.25
A2	2.59	2.69	2.89
b	0.71	0.81	0.96
b1	1.17	1.27	1.37
c	0.31	0.38	0.61
c1	1.17	1.27	1.37
D	8.50	8.70	8.90
D1	6.40		
E	10.01	10.16	10.31
E1	7.6		
E2	9.98	10.08	10.31
e		2.54	
H	14.6	15.1	15.6
L	2.00	2.30	2.74
L1	1.12	1.27	1.42
L2	1.30		2.20
L3		0.25BSC	
e	0	-	8°
e1		5°	
e2		4°	
e3		4°	

**Ordering Information**

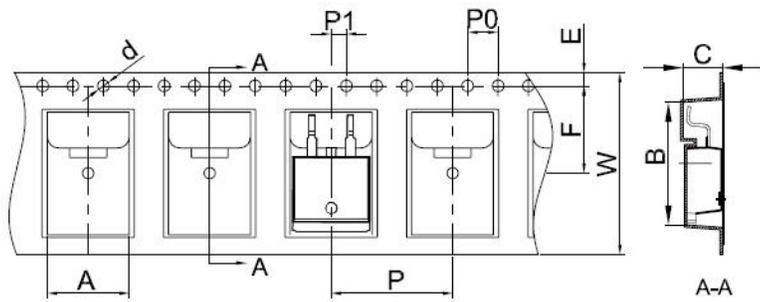
Device	Package	Shipping
STB30H100	D <sup>2</sup> PAK	800pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

**Marking Diagram**


Where XXXXX is YYWWL  
 ST = Device Type  
 B = Package type  
 30 = Forward Current (30A)  
 H = Tj 175°C  
 100 = Reverse Voltage(100V)  
 SSG = SSG  
 YY = Year  
 WW = Week  
 L = Lot Number

**Cautions:** Molding resin  
 Enxxv resin III :94V-0

**Carrier Tape Specification D<sup>2</sup>PAK**


SYMBOL	Millimeters	
	Min.	Max.
A	10.70	10.90
B	16.03	16.23
C	5.11	5.31
d	1.45	1.65
E	1.65	1.85
F	11.40	11.60
P0	3.90	4.10
P	15.90	16.10
P1	1.90	2.10
W	23.90	24.30

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